

BSR16

PNP General Purpose Amplifier

- This device designed for use as general purpose amplifier and switches requiring collector currents to 500mA.
- · Sourced from Process 63.
- See BCW68G for Characteristics.



1. Base 2. Emitter 3. Collector

PNP Epitaxial Silicon Transistor

Absolute Maximum Ratings* Ta=25°C unless otherwise noted

| Symbol | Parameter | Value | Units |
|----------------------------------|--|------------|-------|
| V _{CEO} | Collector-Emitter Voltage | -60 | V |
| V _{CBO} | Collector-Base Voltage | -60 | V |
| V _{EBO} | Emitter-Base Voltage | -5.0 | V |
| Ic | Collector Current - Continuous | -800 | mA |
| T _J , T _{ST} | Operating and Storage Junction Temperature Range | -55 ~ +150 | °C |

^{*} These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

These ratings are based on a maximum junction temperature of 150 degrees C.
These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

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| Symbol | Parameter | Test Condition | Min. | Тур. | Max. | Units |
|-----------------------|--------------------------------------|--|-------------------------------|------|--------------|----------|
| Off Charact | eristics | | | | | • |
| BV _{(BR)CEO} | Collector-Emitter Breakdown Voltage | $I_C = -10 \text{mA}, I_B = 0$ | -60 | | | V |
| BV _{(BR)CBO} | Collector-Base Breakdown Voltage | $I_C = -100\mu A, I_E = 0$ | -60 | | | V |
| BV _{(BR)EBO} | Emitter-Base Breakdown Voltage | $I_E = -10\mu A, I_C = 0$ | -5.0 | | | V |
| I _{CBO} | Collector Cut-off Current | V _{CB} = -50V V _{CB} = -50V, T _A = 150°C | | | -10 -10 | nA μA |
| I _{CEX} | Collector Cut-off Current | $V_{CE} = -30V, V_{EB} = -0.5V$ | | | -50 | nA |
| I _{BEX} | Reverse Base Current | $V_{CE} = -30V, V_{EB} = -3.0V$ | | | -50 | nA |
| On Charact | eristics | | | | | • |
| h _{FE} | DC Current Gain | $\begin{split} I_C &= -0.1 \text{mA}, \ V_{CE} = -10 \text{V} \\ I_C &= -1.0 \text{mA}, \ V_{CE} = -10 \text{V} \\ I_C &= -10 \text{mA}, \ V_{CE} = -10 \text{V} \\ I_C &= -150 \text{mA}, \ V_{CE} = -10 \text{V} \\ I_C &= -500 \text{mA}, \ V_{CE} = -10 \text{V} \\ \end{split}$ | 75 100 100 100 50 | 300 | | |
| V _{CE} (sat) | Collector-Emitter Saturation Voltage | I _C = -150mA, I _B = -15mA I _C = -500mA, I _B = -50mA | | | -0.4 -1.6 | V V |
| V _{BE} (sat) | Base-Emitter Saturation Voltage | $I_C = -150 \text{mA}, I_B = -15 \text{mA}$ $I_C = -500 \text{mA}, I_B = -50 \text{mA}$ | | | -1.3 -2.6 | V V |
| Small Signa | al Characteristics | | | | | • |
| f _T | Current Gain Bandwidth Product | I _C = -50mA, V _{CE} = -20V, f = 100MHz, T _A = 25°C | 200 | | | MHz |
| C _{cb} | Output Capacitance | $V_{CB} = -10V, I_E = 0, f = 1.0MHz$ | | | 8.0 | pF |
| C _{eb} | Emitter-Base Capacitance | $V_{CB} = -2.0V$, $I_E = 0$, $f = 1.0MHz$ | | | 30 | pF |
| Switching (| Characteristics | | | | | |
| t _{on} | Turn-On Time | $V_{CC} = -30V, I_{C} = -150mA,$ | | | 45 | ns |
| t _d | Delay Time | I _{B1} = -15mA | | | 10 | ns |
| t _r | Rise Time | | | | 40 | ns |
| t _{off} | Turn-Off Time | $V_{CC} = -30V, I_{C} = -150mA,$ | | | 100 | ns |
| t _s | Storage Time | $I_{B1} = I_{B2} = -15mA$ | | | 80 | ns |
| | | | | | | |

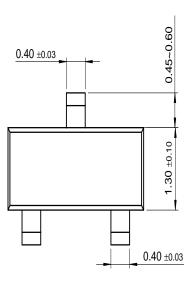
Thermal Characteristics $\rm T_A=25^{\circ}C$ unless otherwise noted

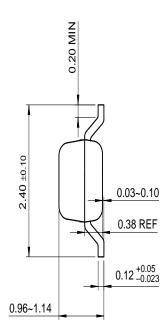
| Symbol | Parameter | Max. | Units |
|-----------------|---|------|-------|
| P _D | Total Device Dissipation | 350 | mW |
| | Derate above 25°C | 2.8 | mW/°C |
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient | 357 | °C/W |

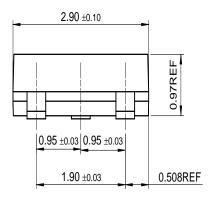
^{*} Device mounted on FR-4 PCB 40mm × 40mm × 1.5mm

Package Dimensions

SOT-23







Dimensions in Millimeters

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